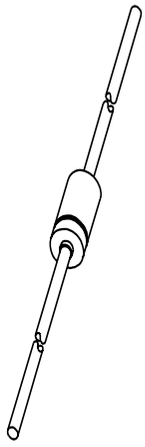
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DATA SHEET



BAS45A
Low-leakage diode

Product data sheet
Supersedes data of June 1994

1996 Mar 13

founded by Philips

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Low-leakage diode BAS45A

FEATURES

- Continuous reverse voltage: max. 125 V
- Repetitive peak forward current: max. 625 mA
- Low reverse current: max. 1 nA
- Switching time: typ. 1.5 μs.

APPLICATION

- Low leakage current applications.

DESCRIPTION

Epitaxial medium-speed switching diode with a low leakage current in a hermetically-sealed glass SOD68 (DO-34) package.

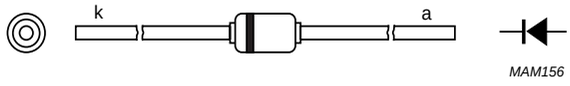


Fig.1 Simplified outline (SOD68; DO-34) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	125	V
V_R	continuous reverse voltage		–	125	V
I_F	continuous forward current	see Fig.2; note 1	–	250	mA
I_{FRM}	repetitive peak forward current		–	625	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t_p = 1 μs	–	4	A
		t_p = 1 ms	–	1	A
		t_p = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	–	300	mW
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature		–	175	°C

Note

1. Device mounted on a printed-circuit board without metallization pad.

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ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	780	mV
		I_F = 10 mA	–	860	mV
		I_F = 100 mA	–	1000	mV
I_R	reverse current	see Fig.5			
		V_R = 125 V; E_{max} = 100 lx	–	1	nA
		V_R = 30 V; T_j = 125 °C; E_{max} = 100 lx	–	300	nA
		V_R = 125 V; T_j = 125 °C; E_{max} = 100 lx	–	500	nA
		V_R = 125 V; T_j = 150 °C; E_{max} = 100 lx	–	2	µA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	–	4	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	1.5	–	µs

THERMAL CHARACTERISTICS

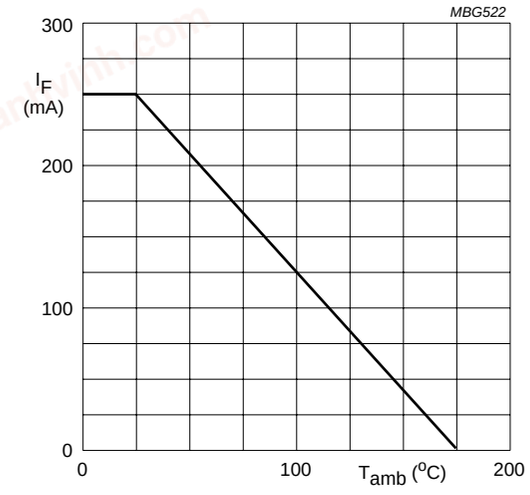
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point	8 mm from the body	300	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

Note

1. Device mounted on a printed-circuit board without metallization pad.

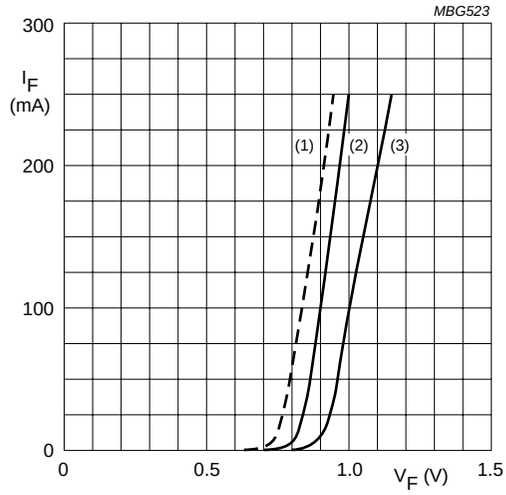
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GRAPHICAL DATA



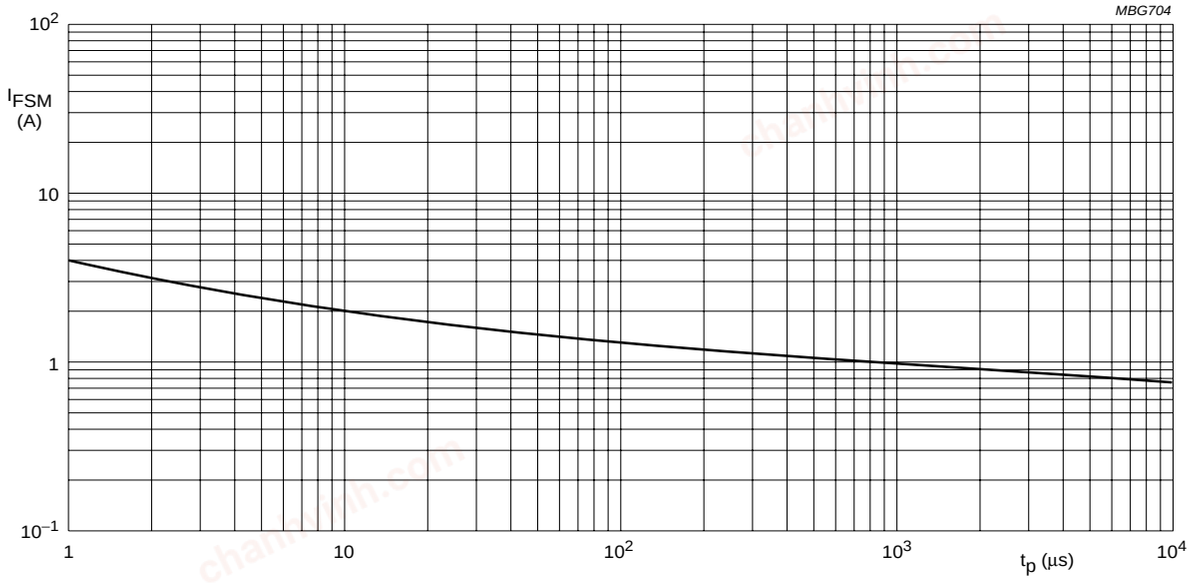
Device mounted on a printed-circuit board without metallization pad.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

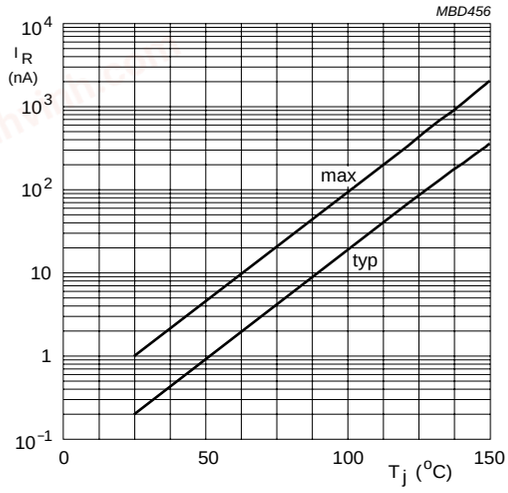
Fig.3 Forward current as a function of forward voltage.



Based on square wave currents; T_j = 25 °C prior to surge.

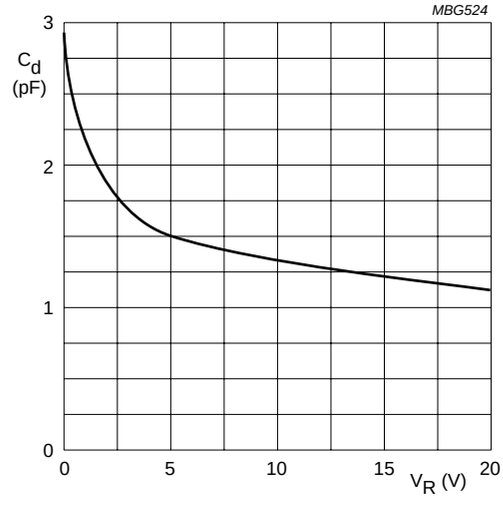
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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V_R = 125 V.

Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

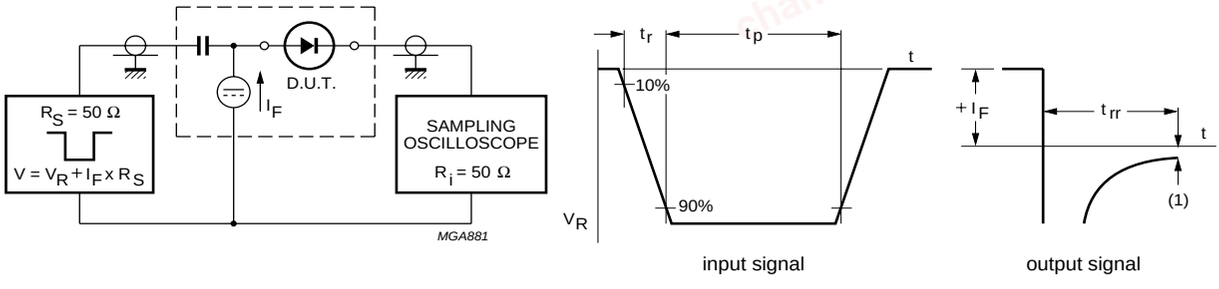
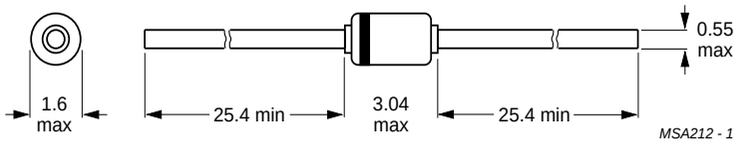


Fig.7 Reverse recovery time test circuit and waveforms.

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PACKAGE OUTLINE



Dimensions in mm.
The black marking band indicates the cathode.

Fig.8 SOD68 (DO-34).

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Low-leakage diode BAS45A

DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS(2)	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

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